

Fig. 1

29 Kvolt

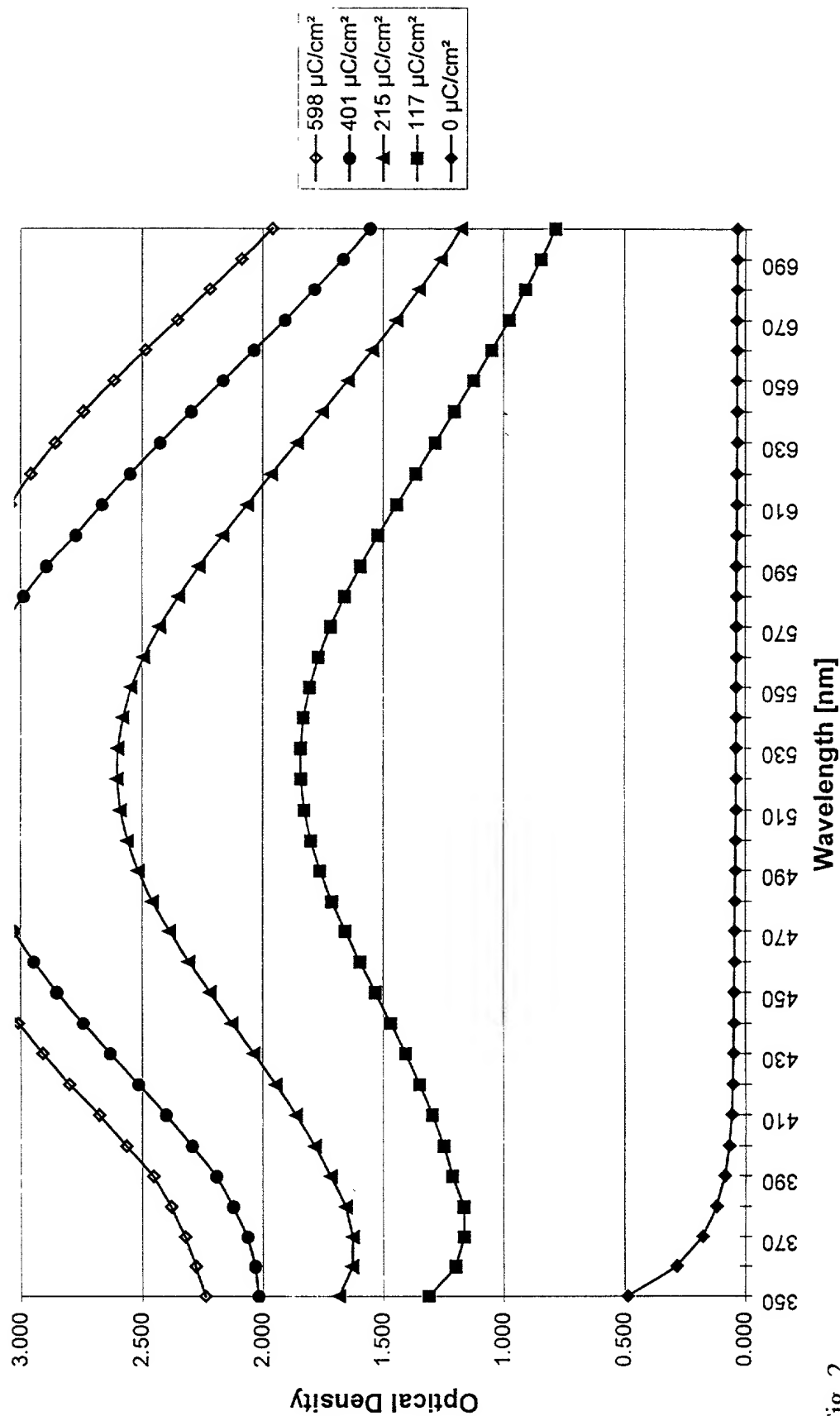


Fig. 2

25 Kvolt

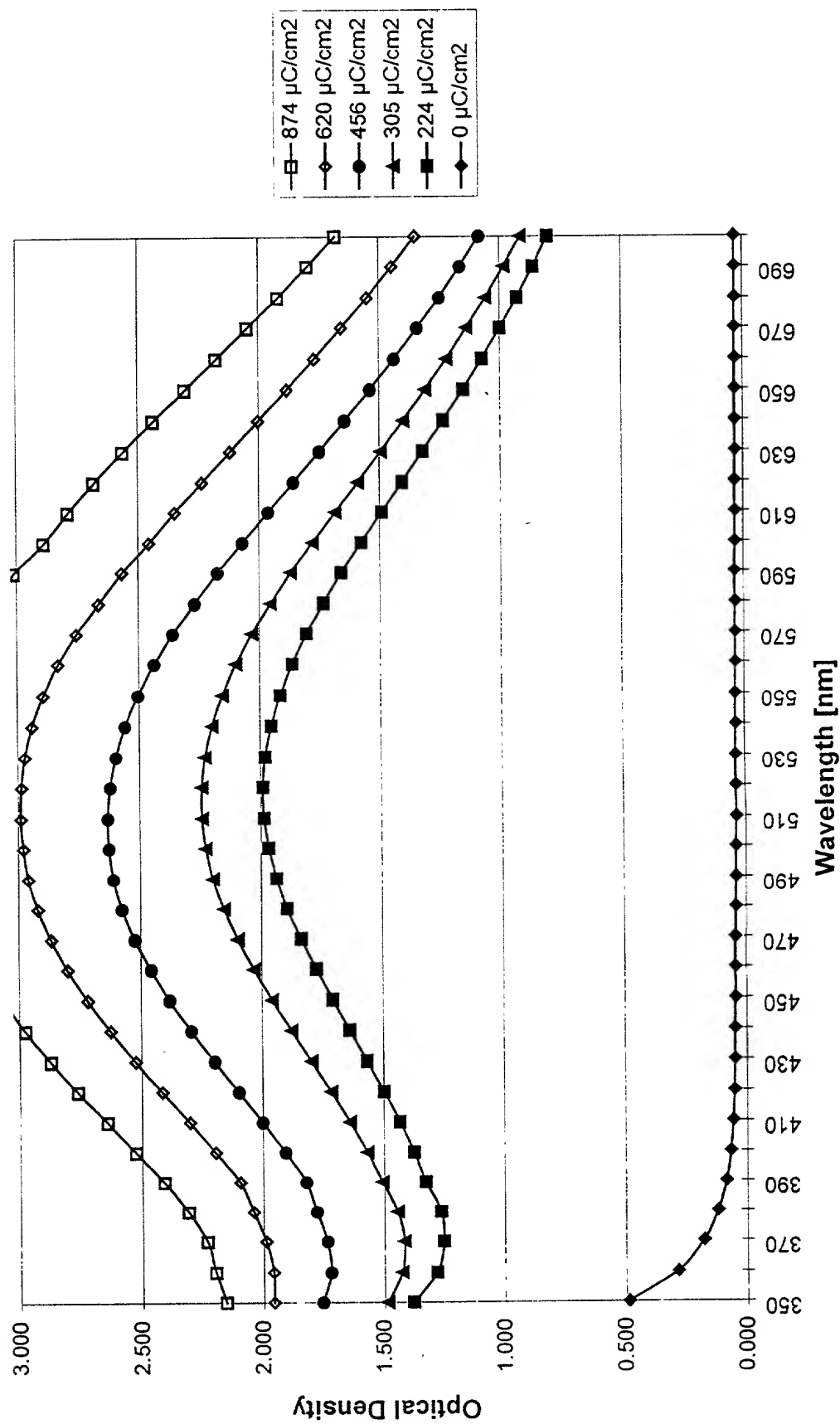


Fig. 3

20 Kvolt

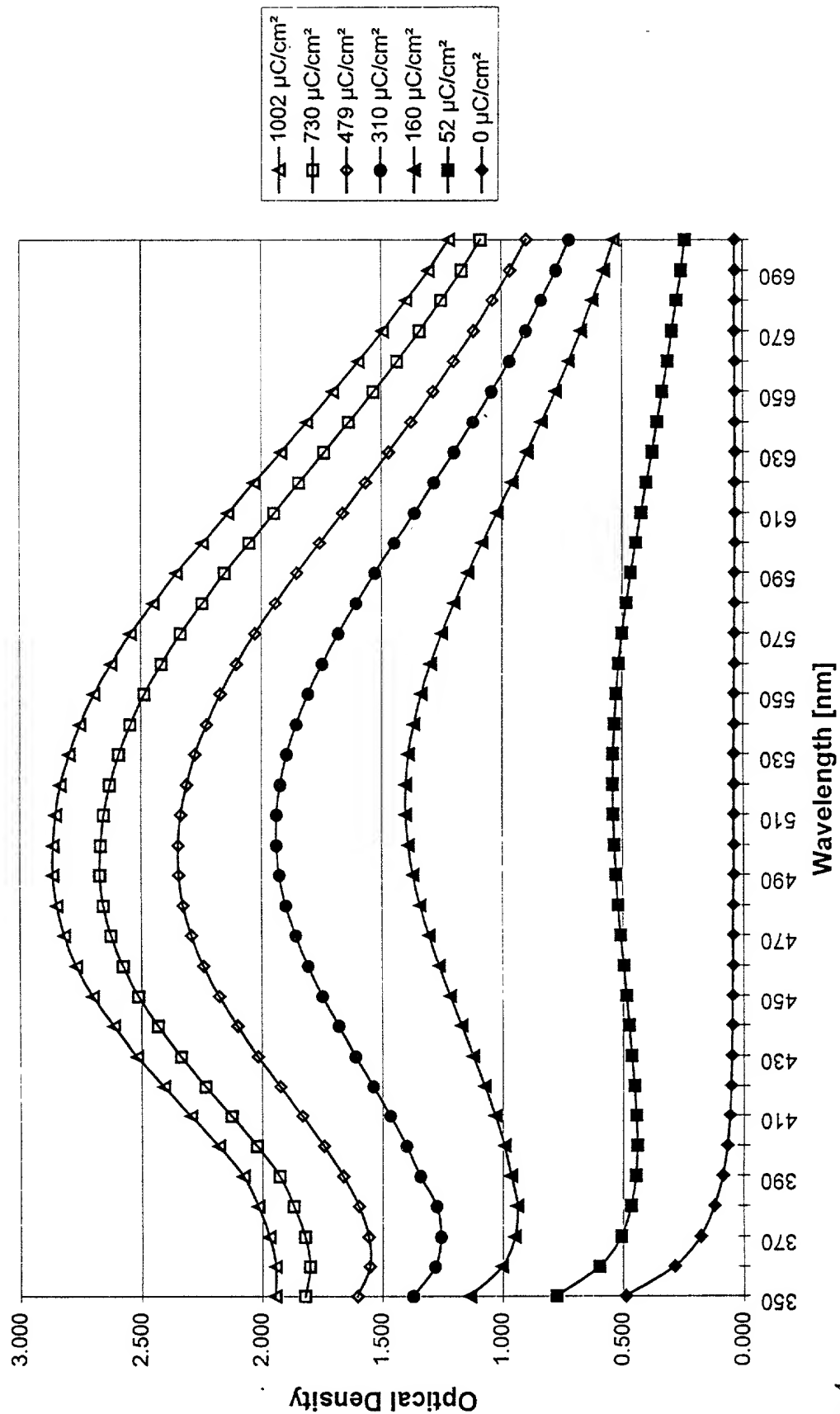


Fig. 4

15 Kvolt

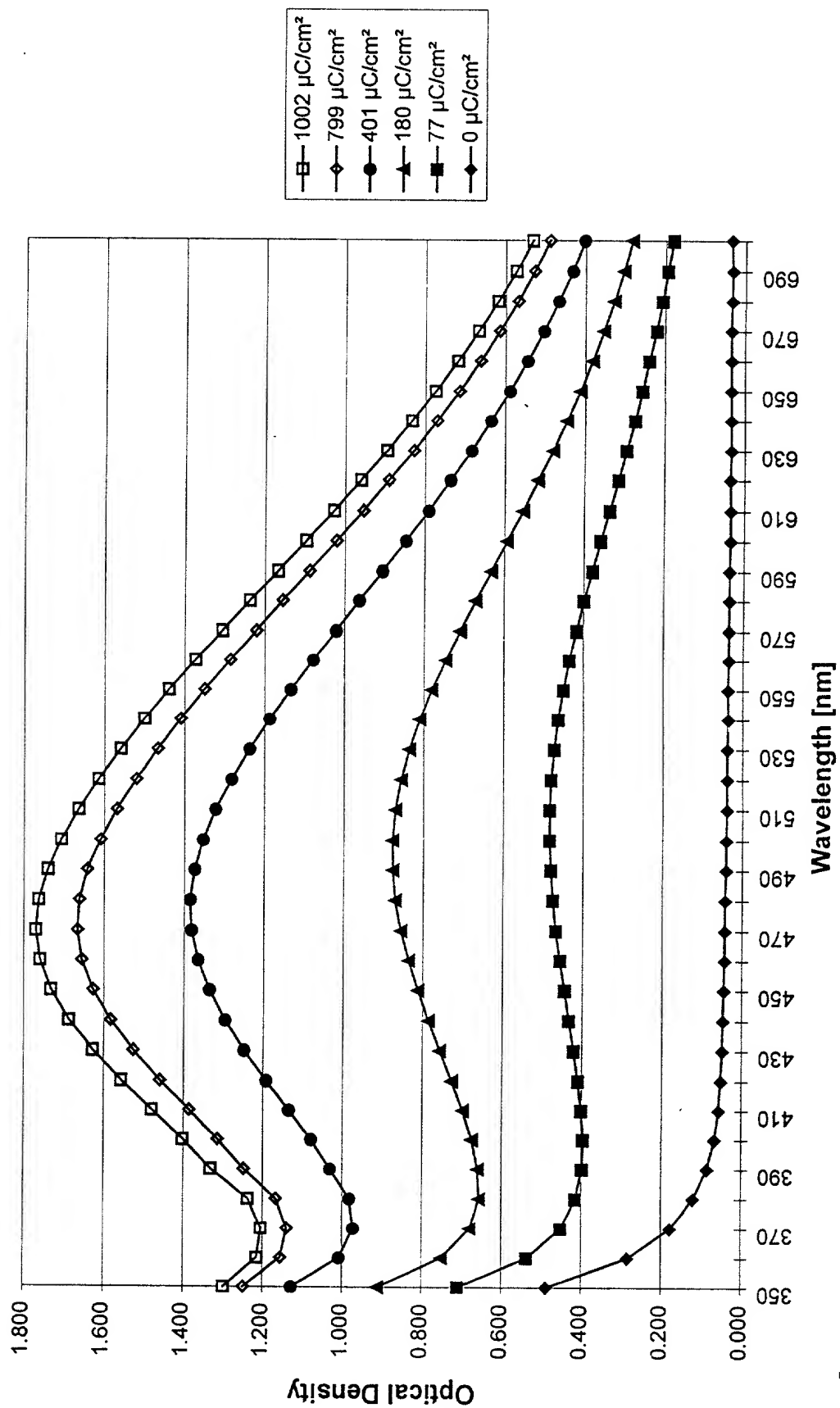


Fig. 5

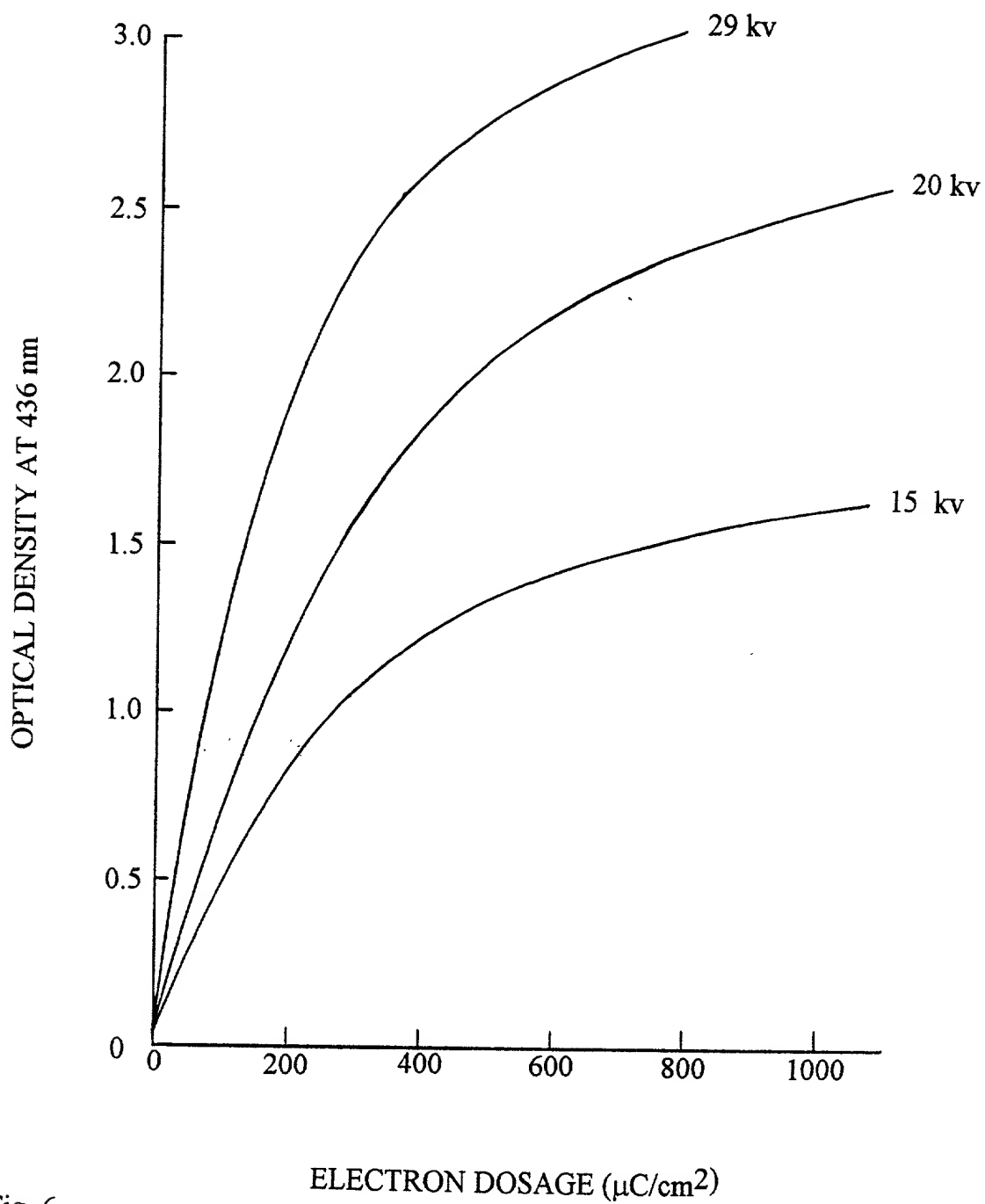


Fig. 6

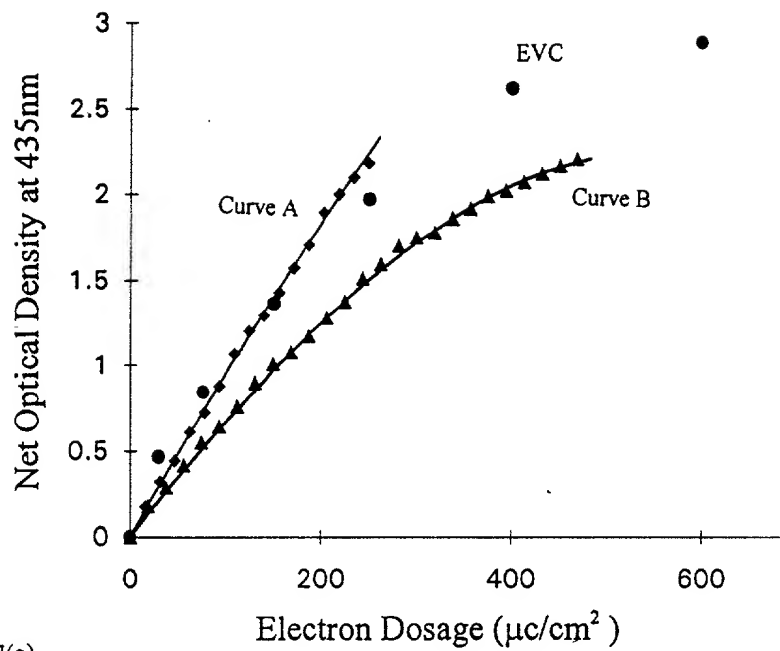


Fig. 7(a)

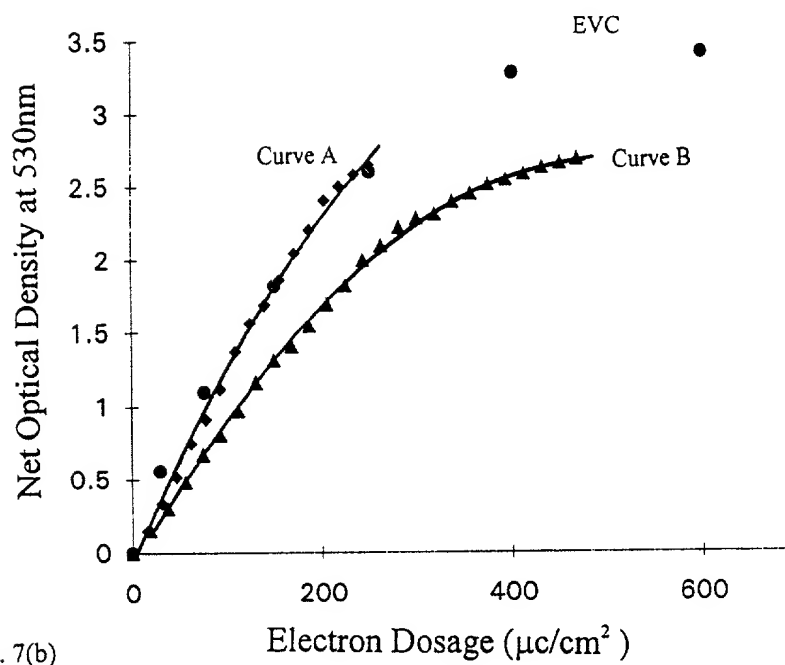


Fig. 7(b)

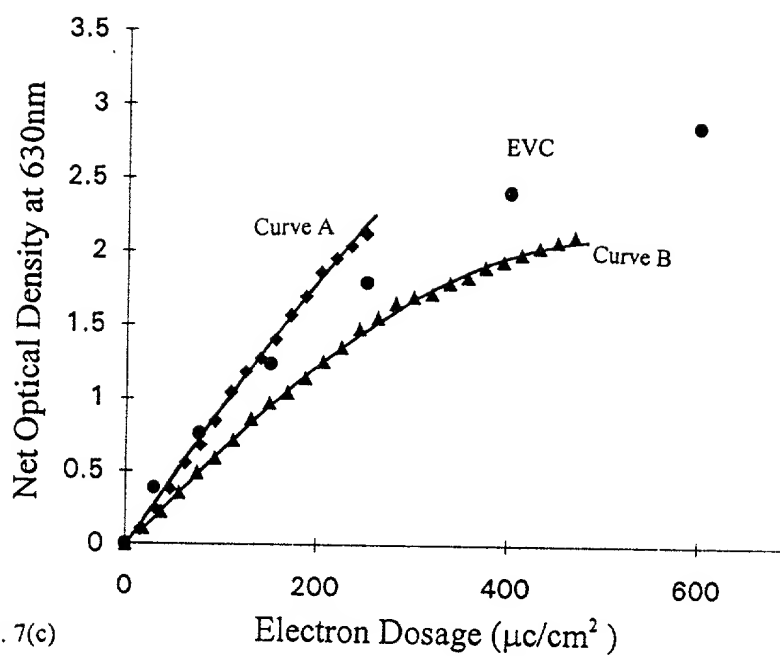


Fig. 7(c)



101280" BT24E660

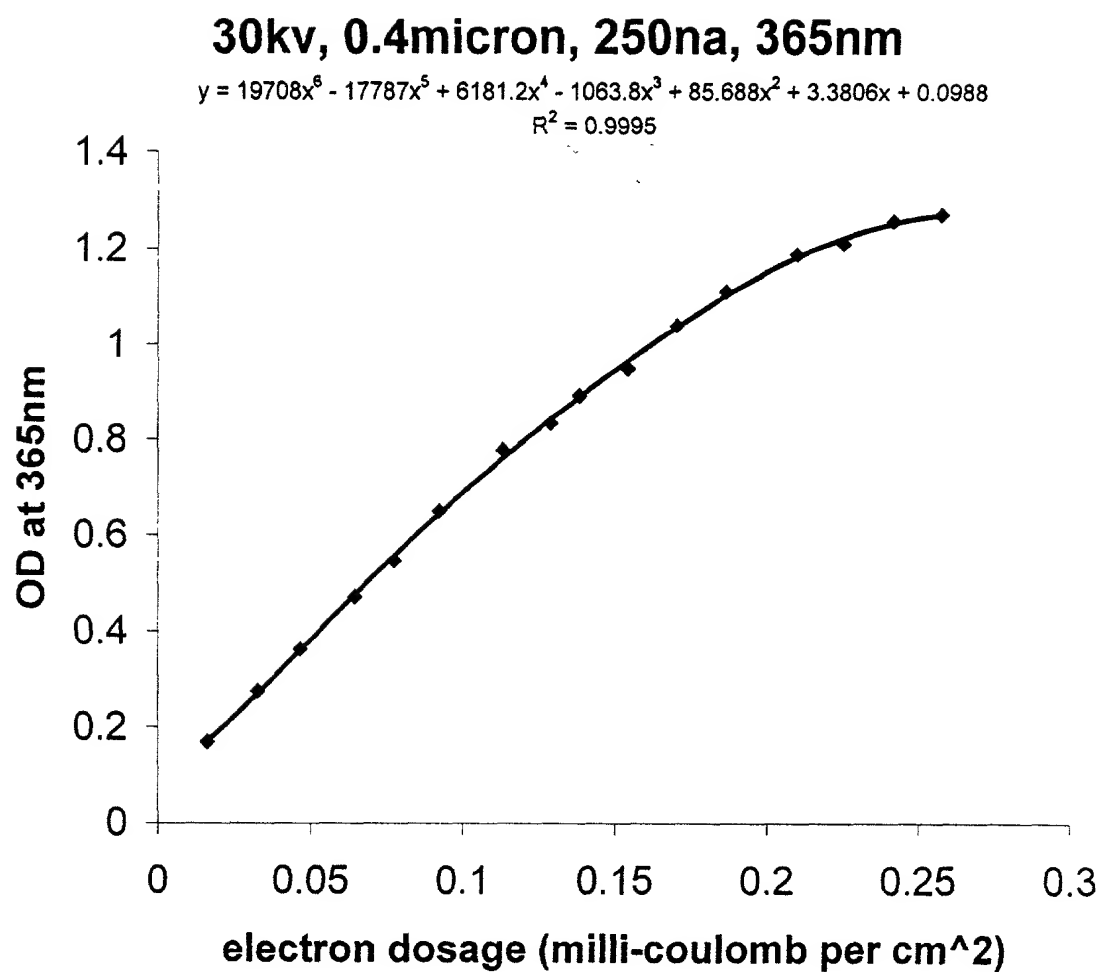


Fig. 7 (d)

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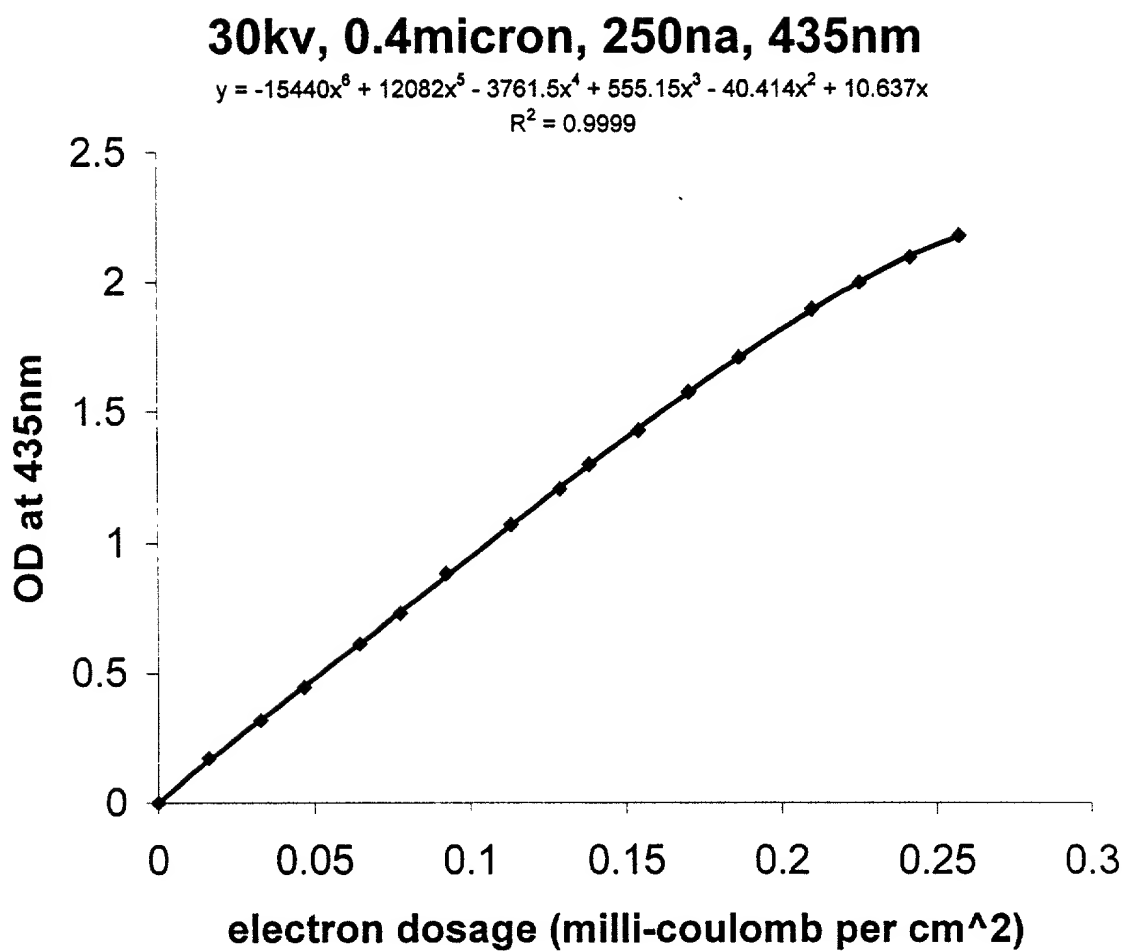


Fig. 7 (e)

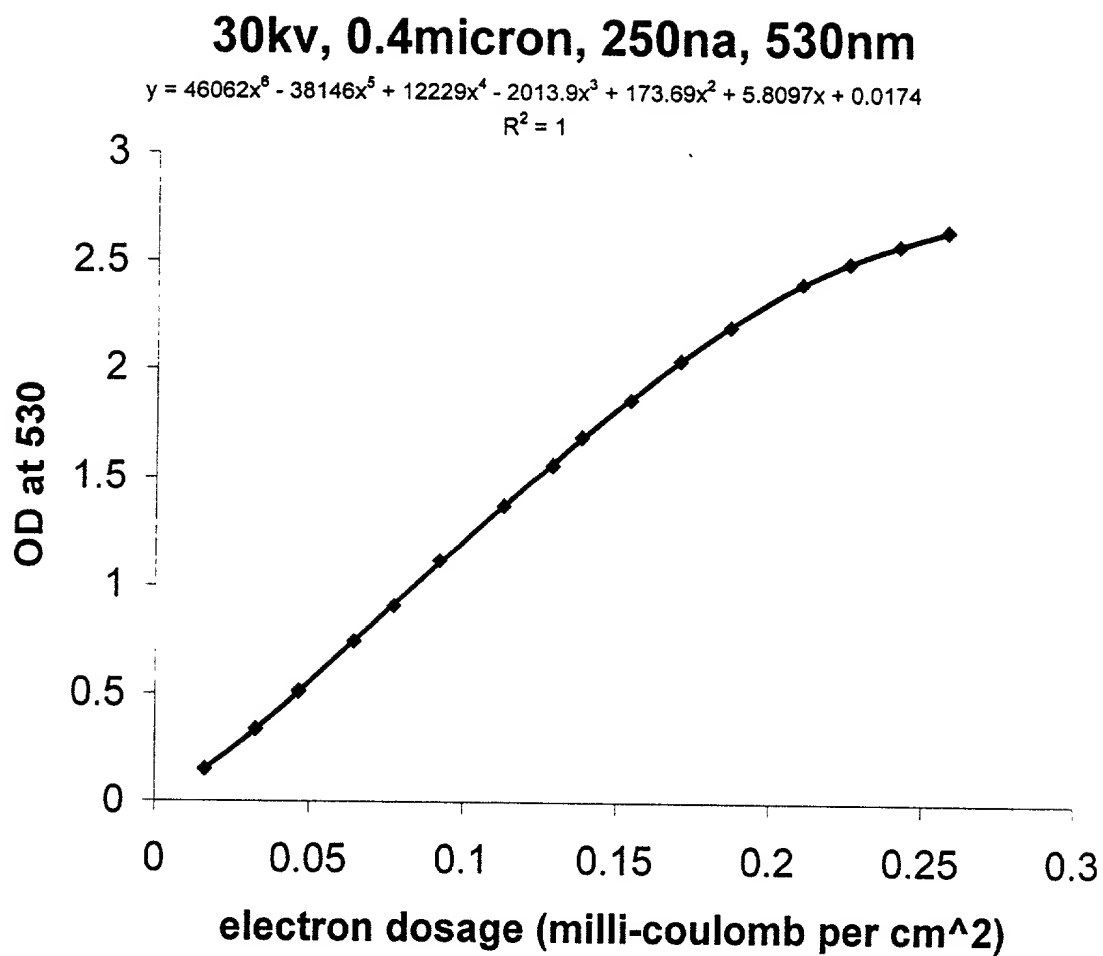


Fig. 7 (f)

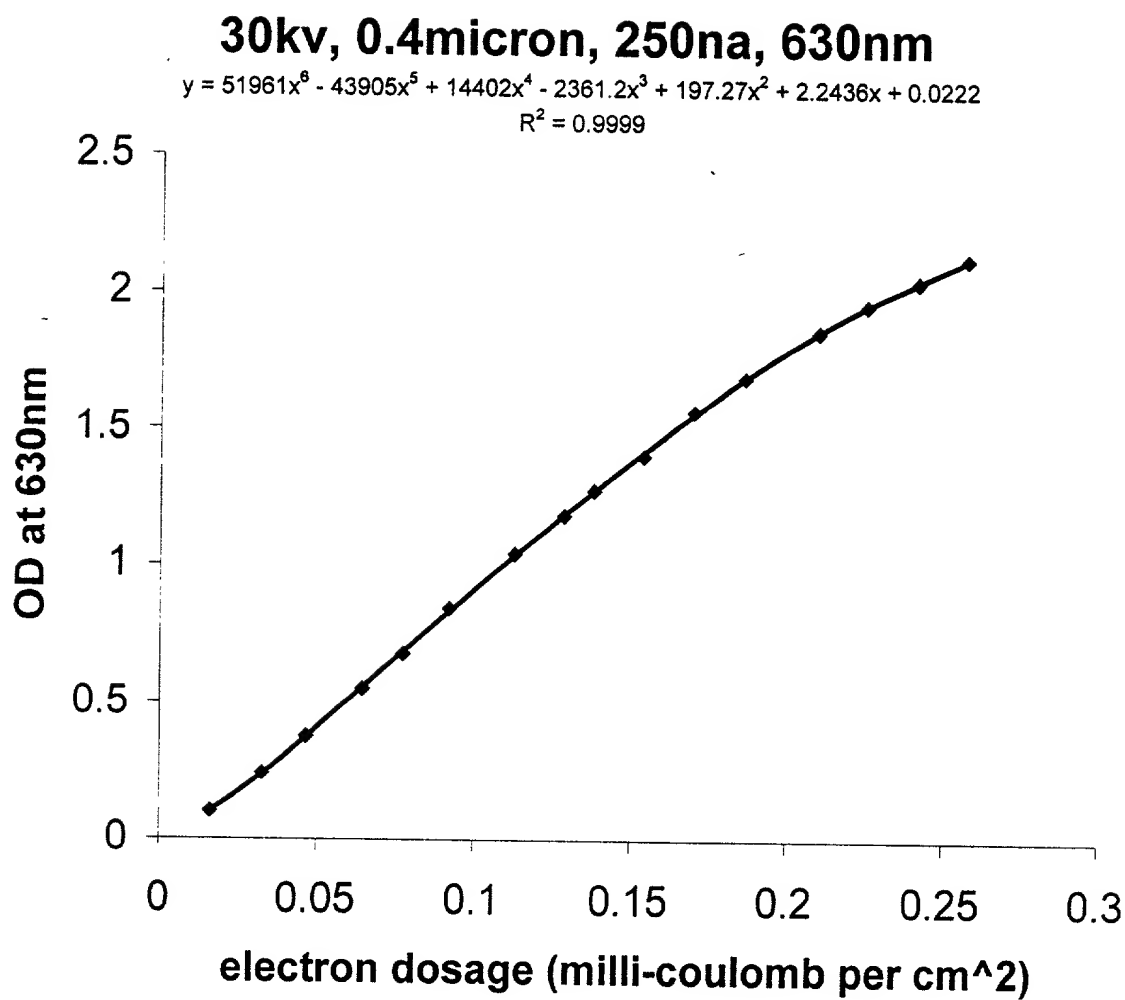


Fig. 7 (g)

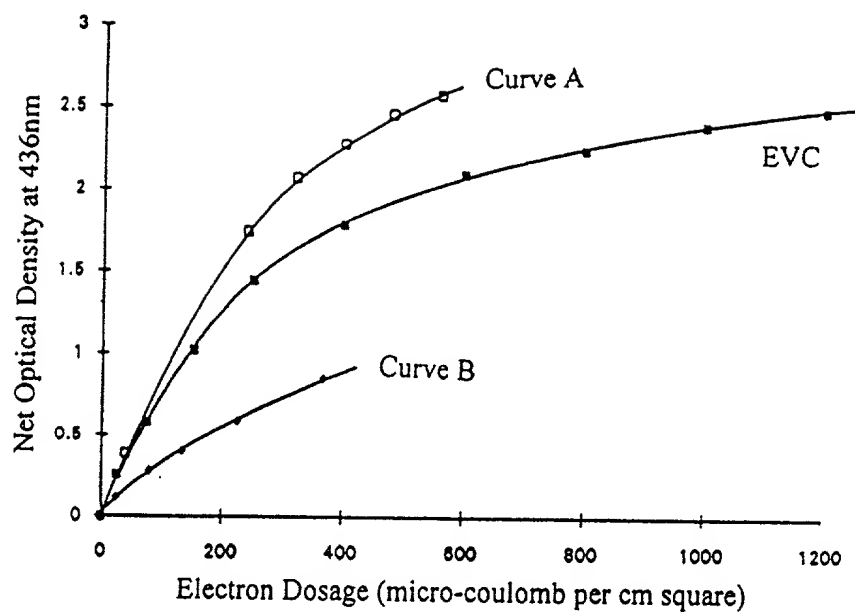


Fig. 8

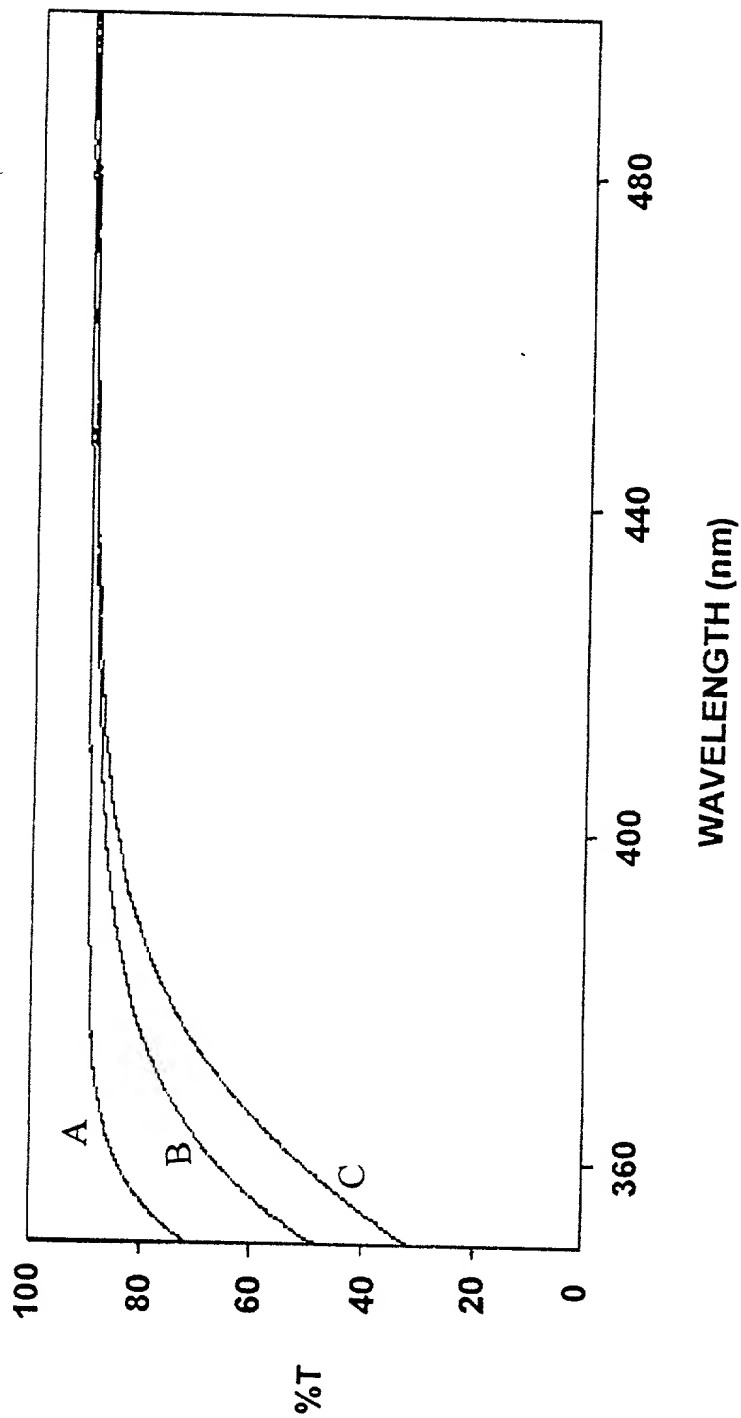


Fig. 9

[illegible]

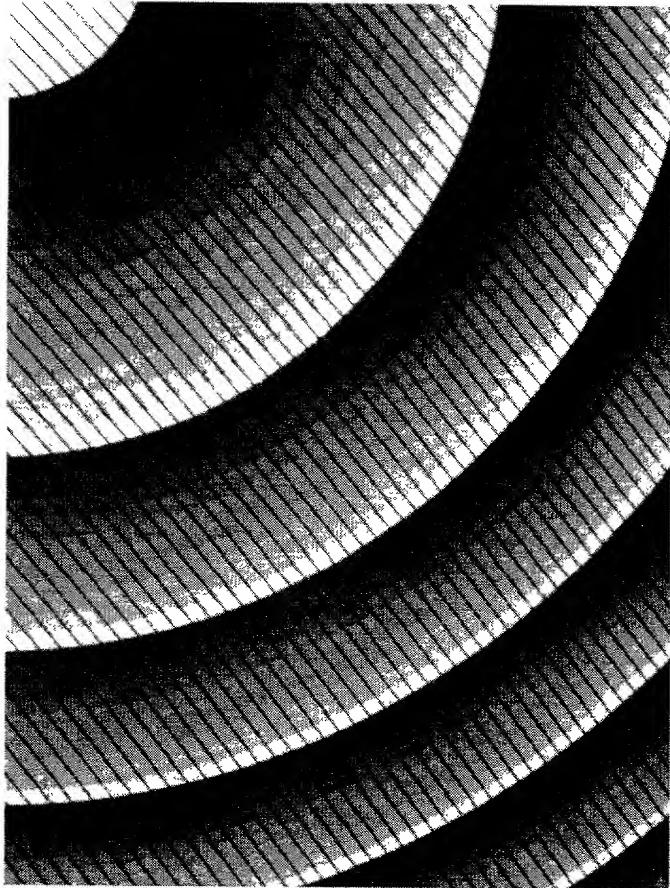


Fig. 11



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a.) HEBS-Glass mask material exposed in e-beam writer



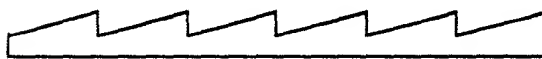
b.) Gray-Level mask generated in HEBS-Glass



c.) Photoresist exposure in optical lithography tool



d.) Resist surface profile after development



e.) Surface profile in substrate material after CAIBE transfer step

Fig. 12



HEBS-Glass material exposed in e-beam writer



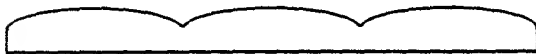
Gray-Level mask generated in HEBS-Glass



Photoresist exposure in mask-aligner



Resist surface profile after development



Lens profile after etching transfer step

Fig. 13

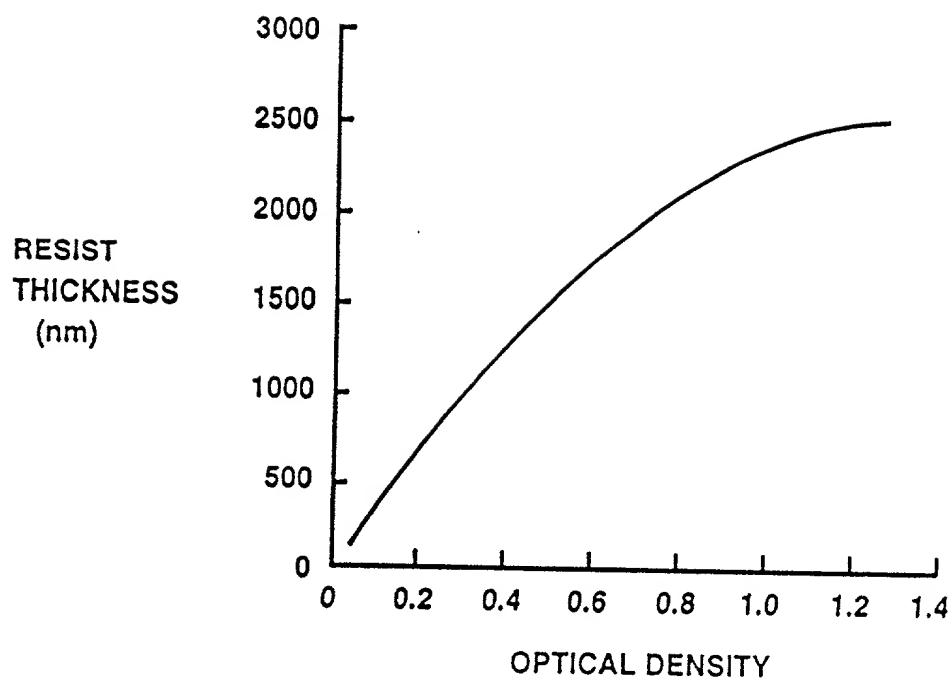


Fig. 14

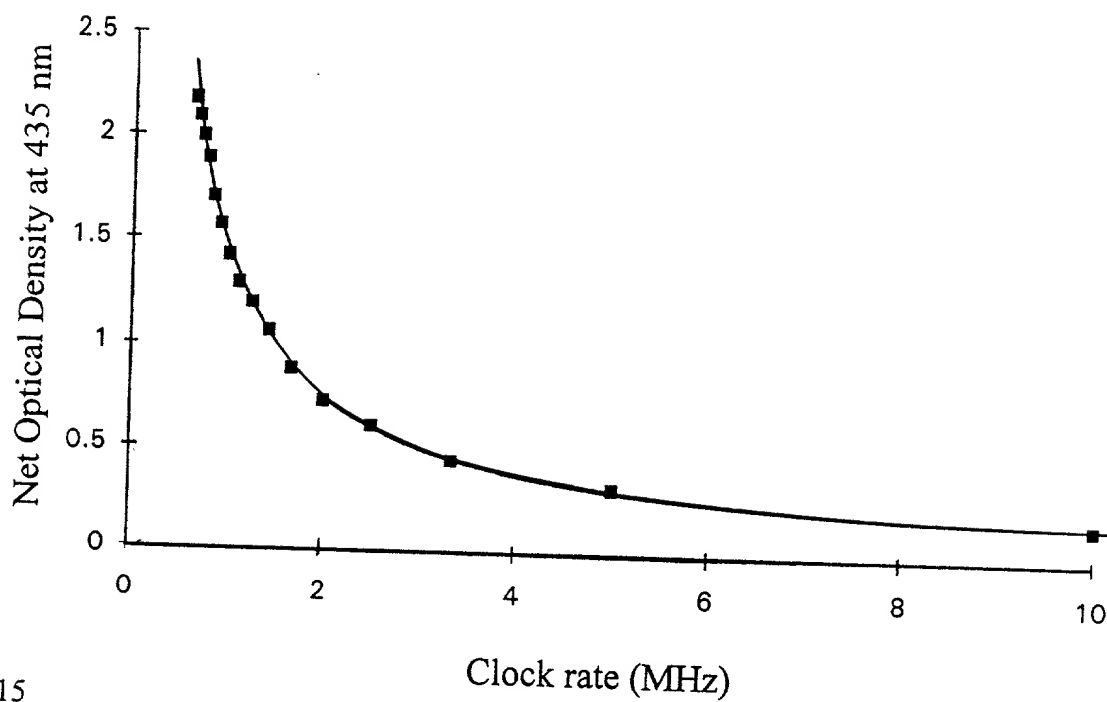


Fig. 15

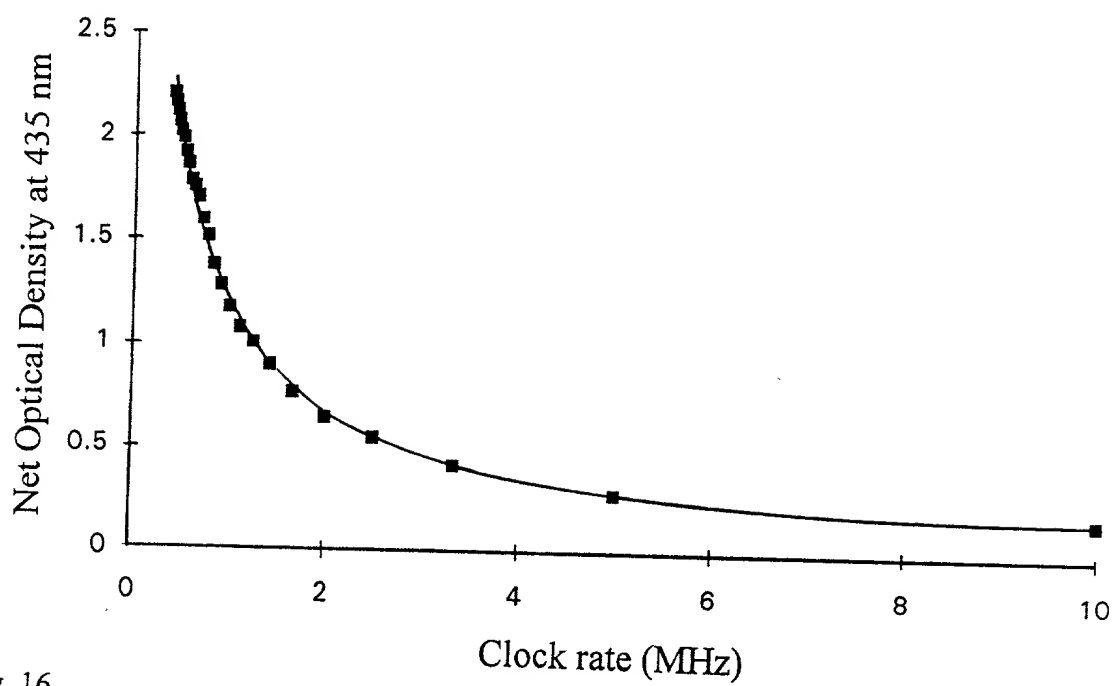


Fig. 16

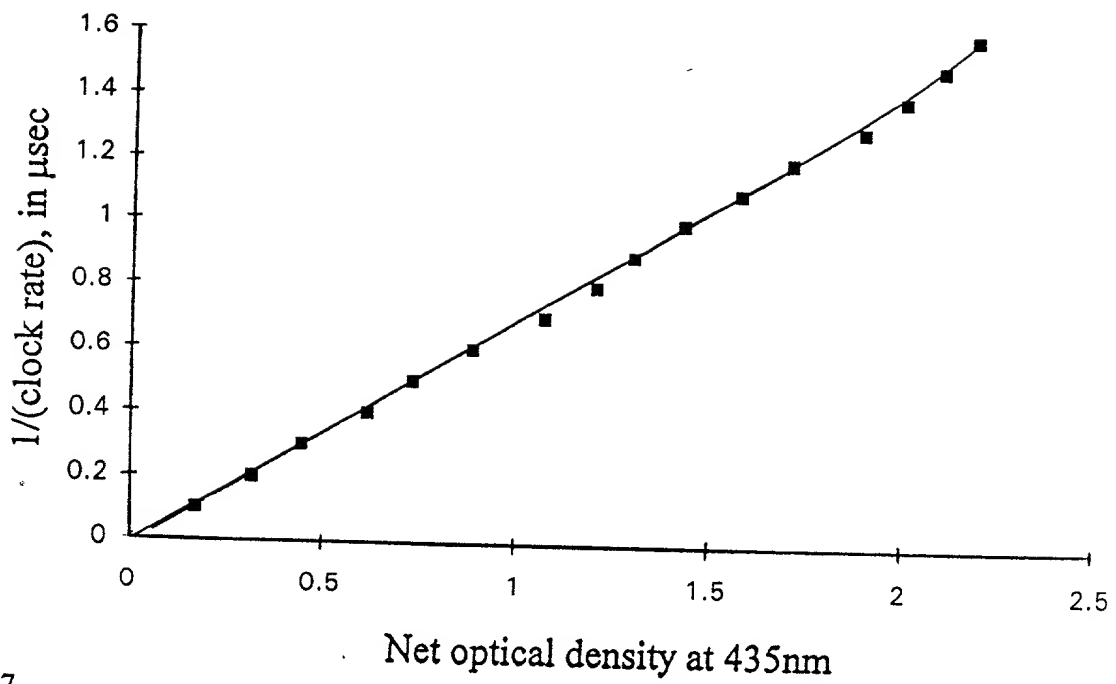


Fig. 17

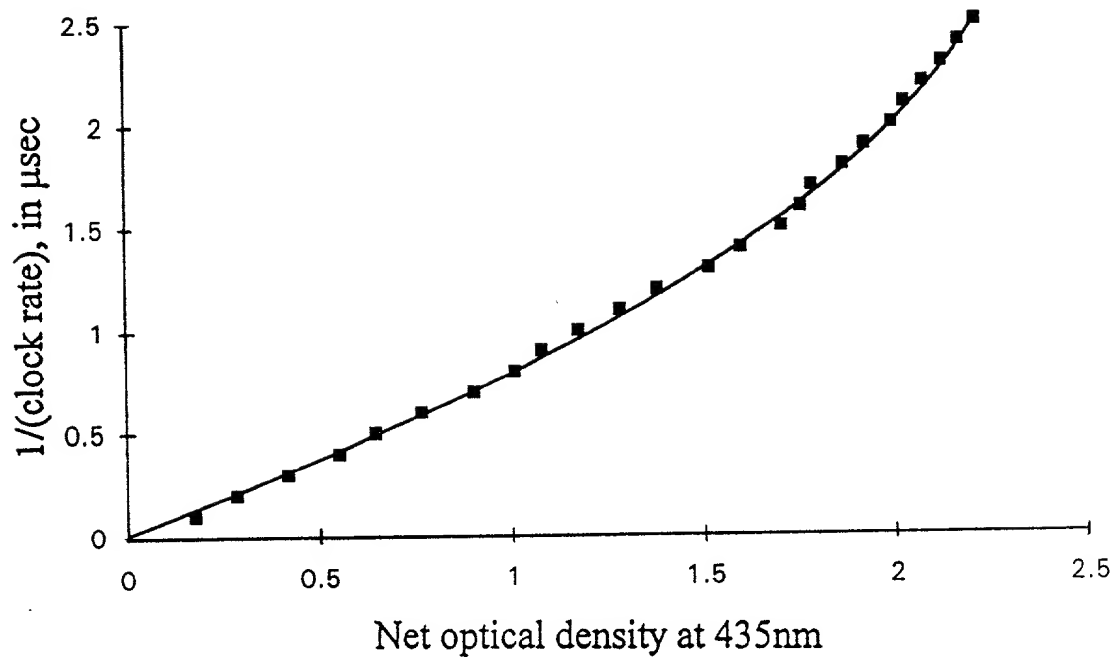


Fig. 18

TOP SECRET

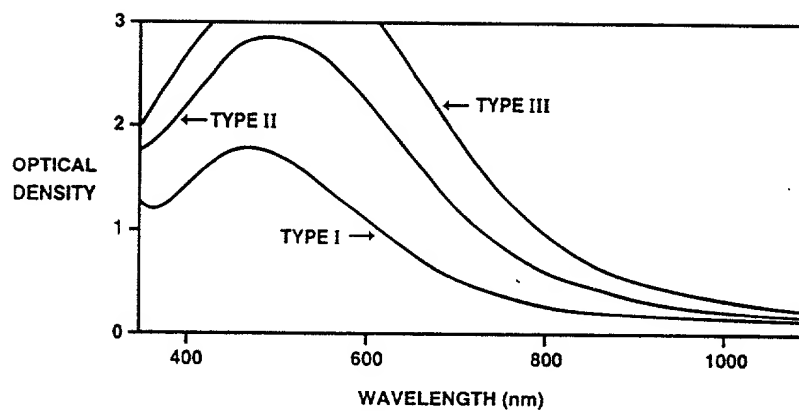


Fig.19

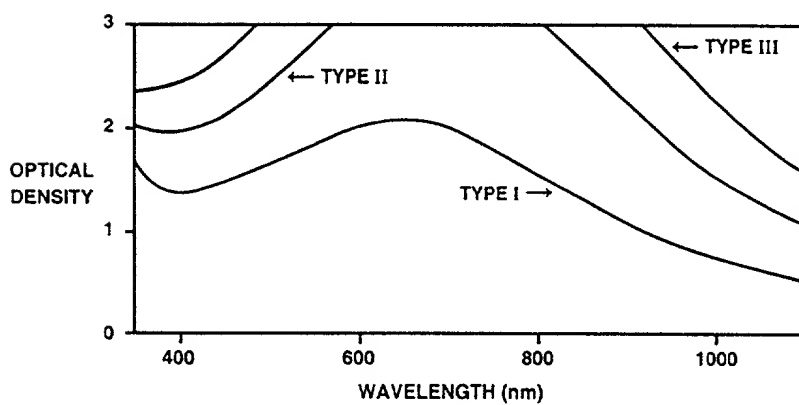


Fig.20



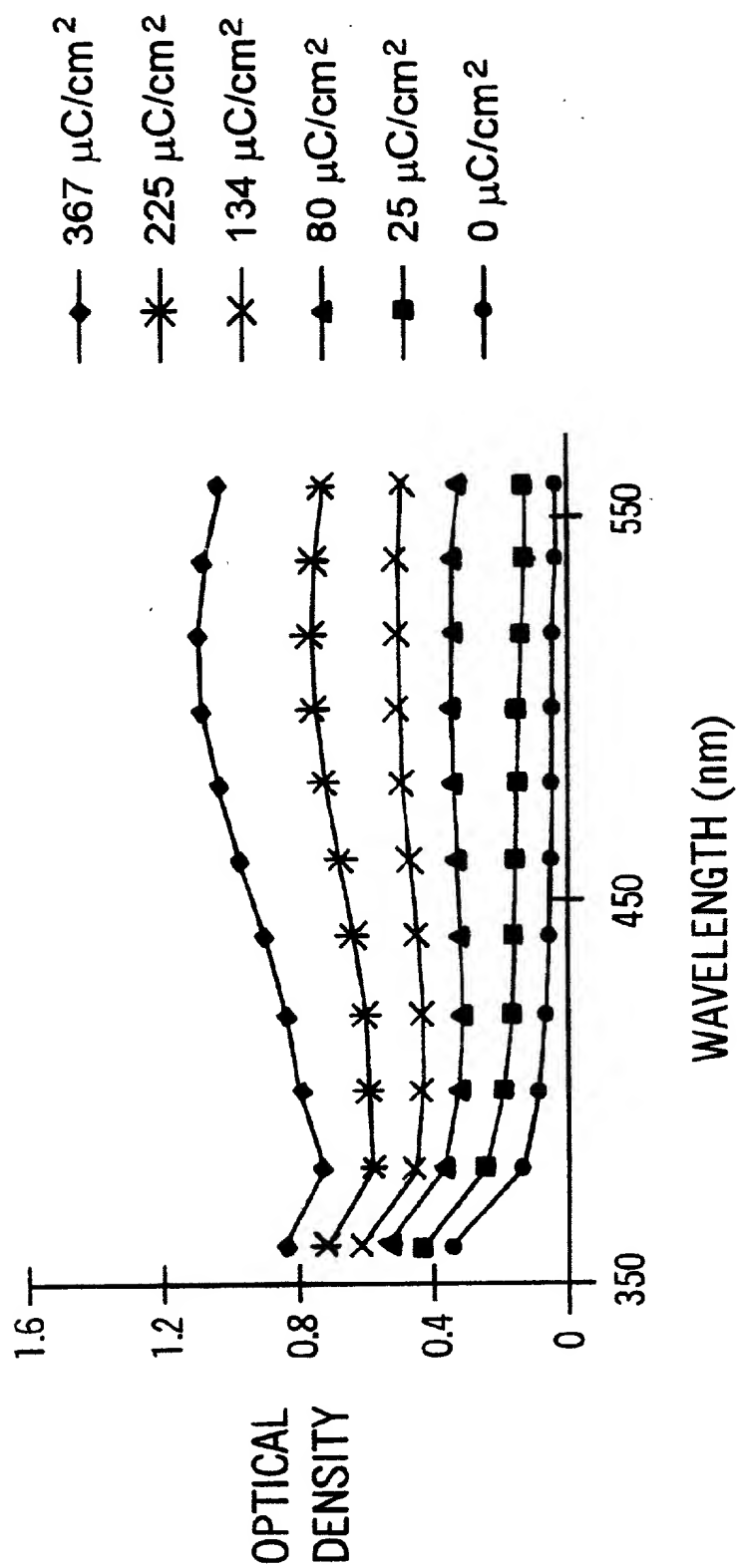


FIG. 21

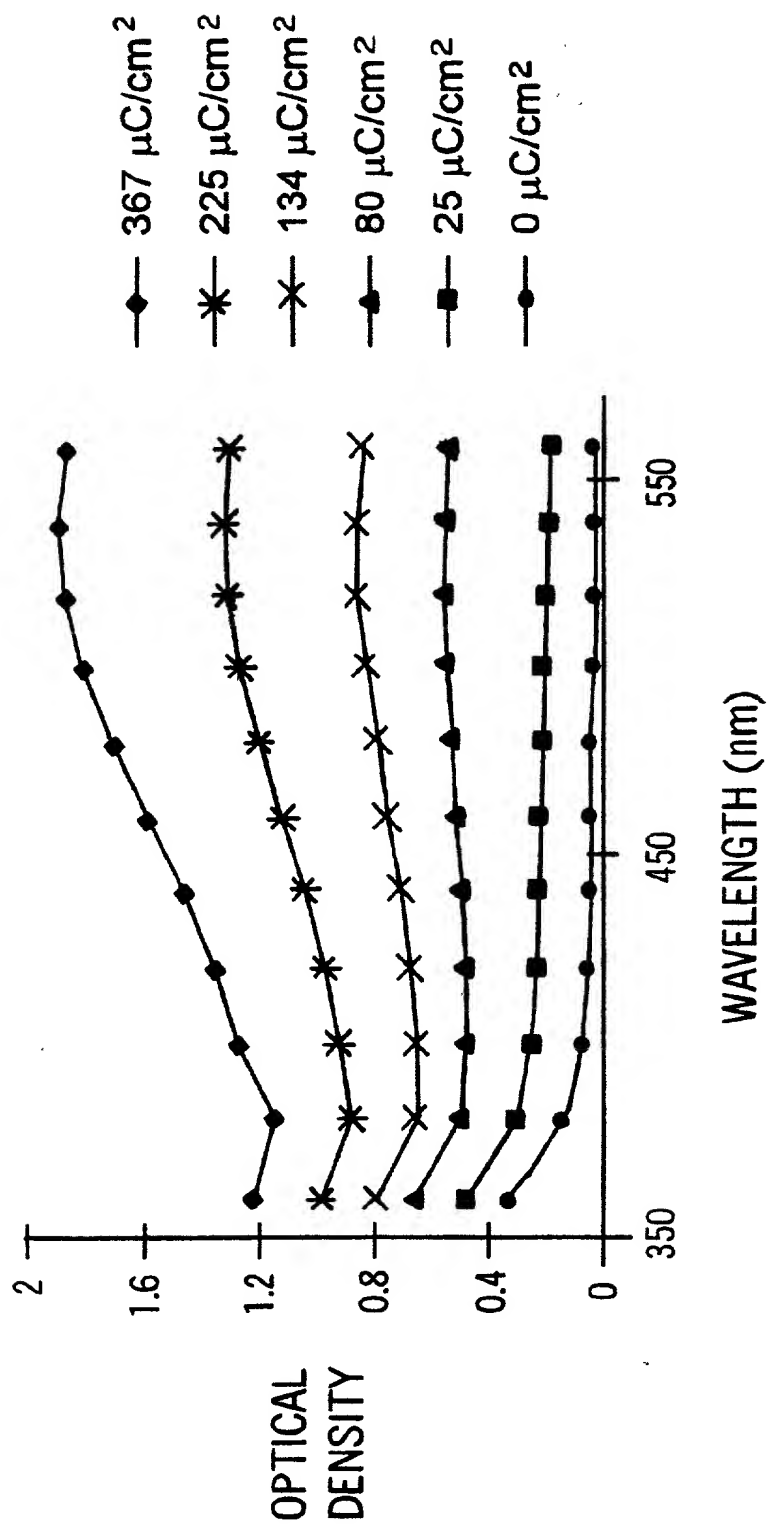


FIG. 22

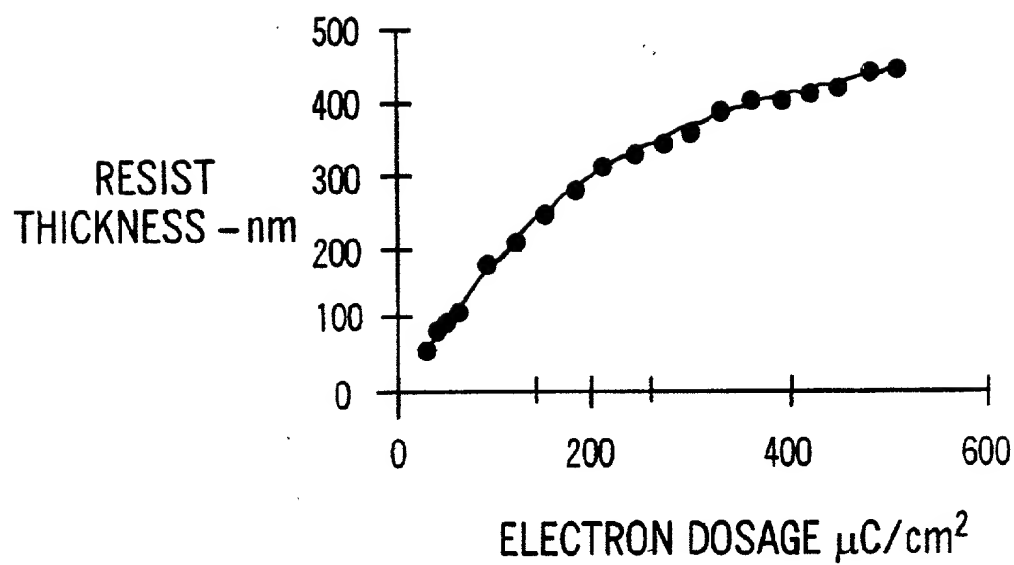


FIG. 23

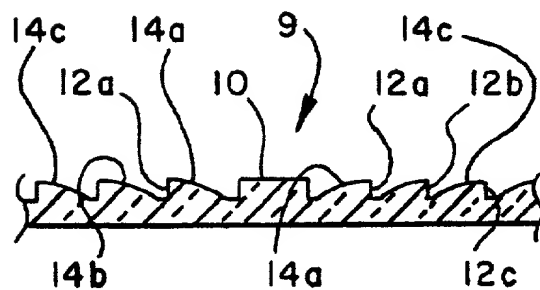


FIG. 24

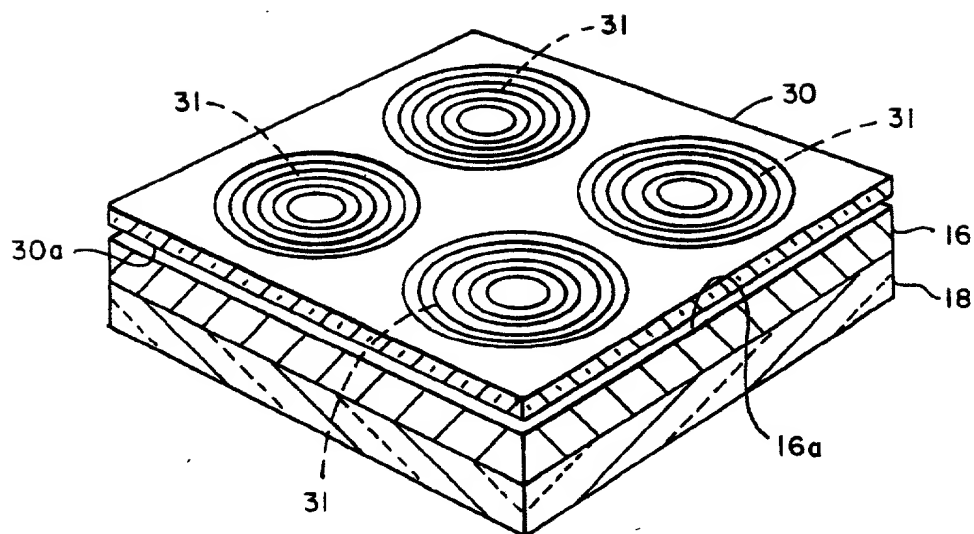


FIG. 25A

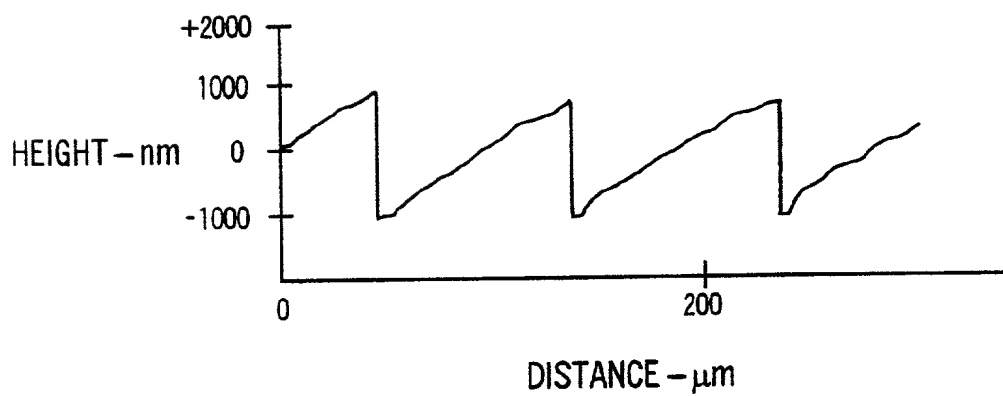


FIG. 25B

